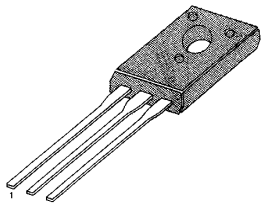
KSE340 NPN EPITAXIAL SILICON TRANSISTOR

HIGH COLLECTOR-EMITTER SUSTAINING VOLTAGE
HIGH VOLTAGE GENERAL PURPOSE APPLICATIONS
SUITABLE FOR TRANSFORMER
Complement to KSE350

TO-126



1. Emitter 2. Collector 3. Base

ABSOLUTE MAXIMUM RATINGS

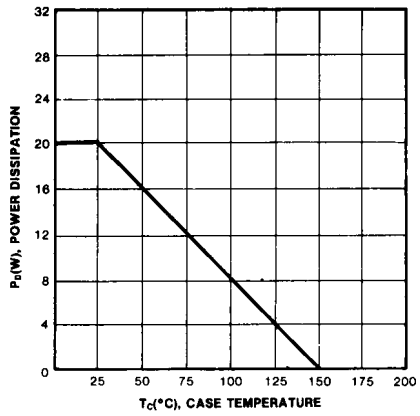
Characteristic	Symbol	Rating	Unit
Collector- Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter- Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Collector Dissipation (T_c=25℃)	P_C	20	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-65 ~ 150	℃

ELECTRICAL CHARACTERISTICS (T_C=25℃)

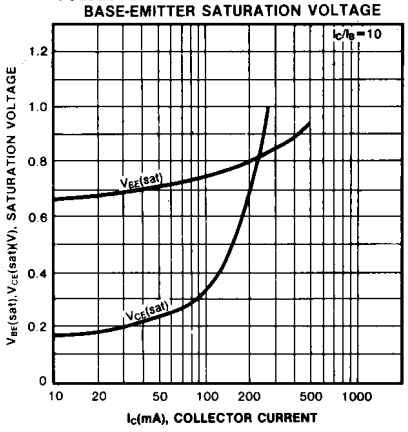
Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Sustaining Voltage	V_{CEO}(sus)	I_C = 1mA, I_B = 0	300		V
Collector Cutoff Current	I_{CBO}	V_{CB} = 300V, I_E =0		100	uA
Emitter Cutoff Current	I_{EBO}	V_{BE} = 3V, I_C = 0		100	uA
DC Current Gain	h_{FE}	V_{CE} = 10V, I_C = 50mA	30	240	

SAMSUNG ELECTRONICS

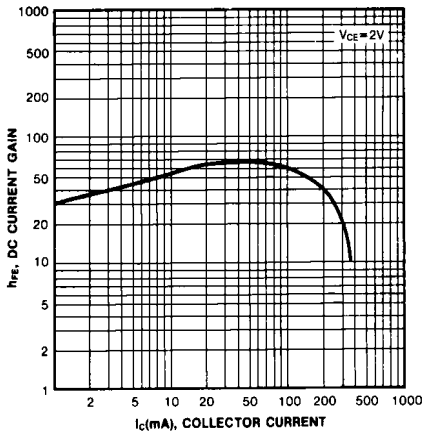
POWER DERATING



COLLECTOR-EMITTER SATURATION VOLTAGE
BASE-EMITTER SATURATION VOLTAGE



DC CURRENT GAIN



FORWARD BIAS SAFE OPERATING AREA